Supplementary Information for

Pressure-Driven Responses in Cd_2SiO_4 and Hg_2GeO_4 Minerals: A Comparative Study

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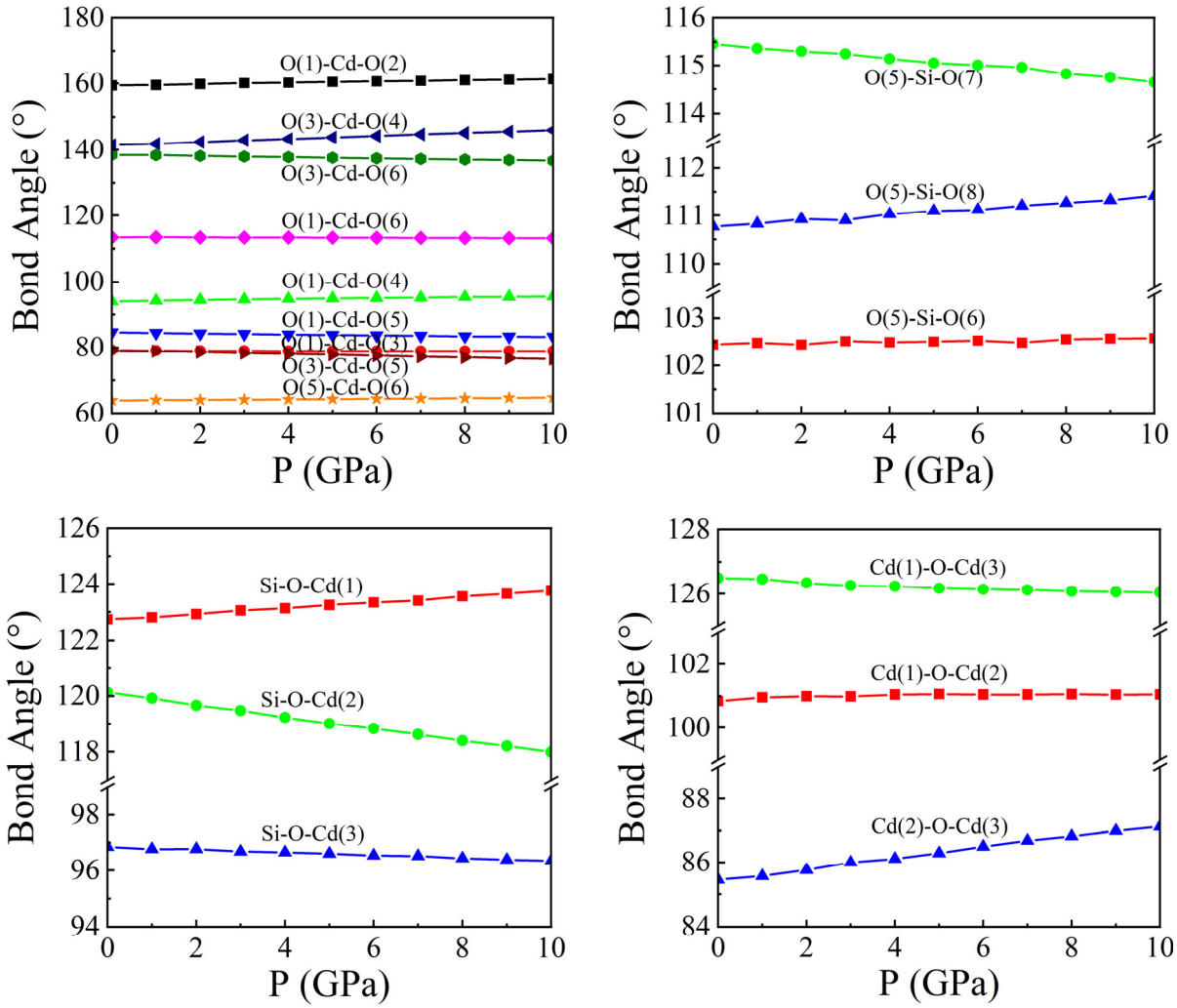


Figure S1. The pressure dependence of selected bond angles of Cd_2SiO_4.

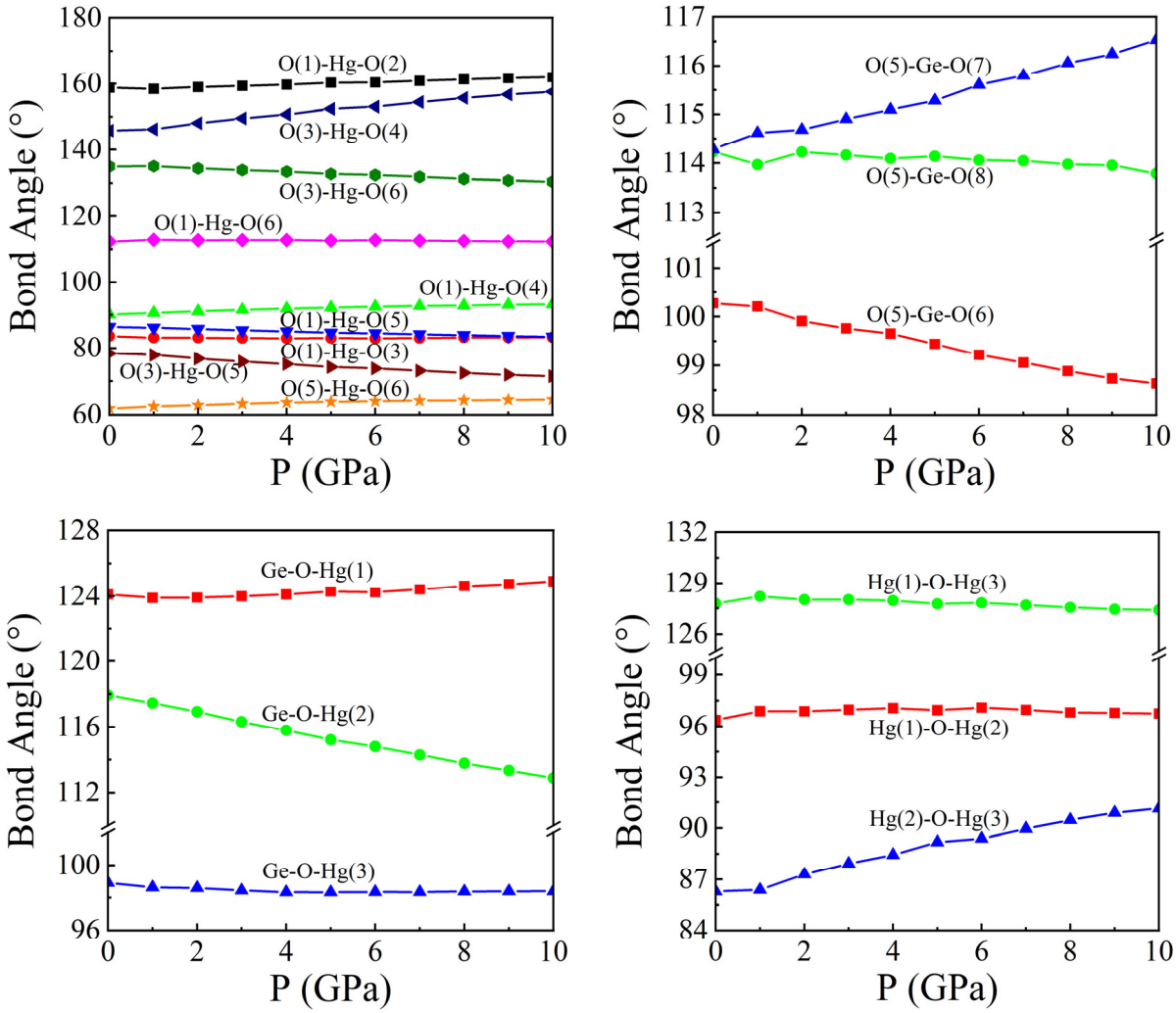


Figure S2. The pressure dependence of selected bond angles of Hg_2GeO_4.